STI6N95K5

N-channel 950 V, 1 Ω typ., 9 A MDmesh™ K5 Power MOSFET in an I²PAK package

Datasheet - production data

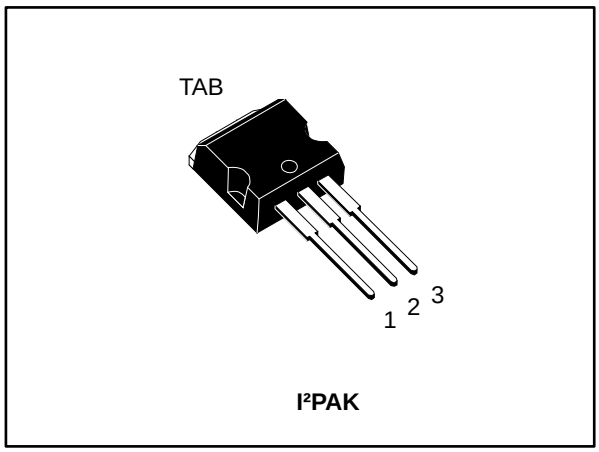
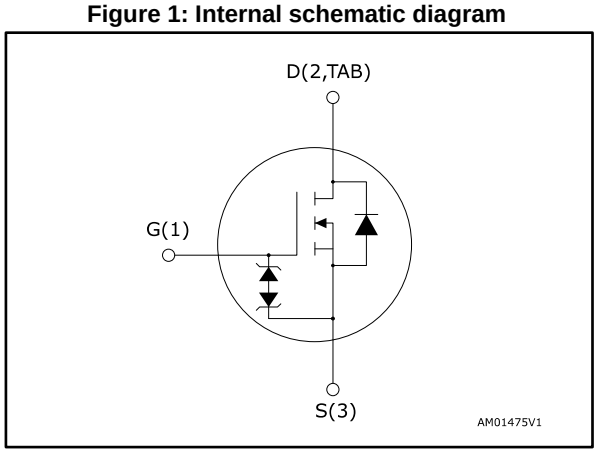


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STI6N95K5	950 V	1.25 Ω	9 A	90 W

- Industry's lowest $R_{DS(on)}$ x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STI6N95K5	6N95K5	I²PAK	Tube

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	9	A
I_D	Drain current (continuous) at T_C = 100 °C	6	A
I_{DM} (1)	Drain current (pulsed)	36	A
P_{TOT}	Total dissipation at T_C = 25 °C	90	W
dv/dt (2)	Peak diode recovery voltage slope	4.5	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	
T_j	Operating junction temperature range	- 55 to 150	°C
T_{stg}	Storage temperature range		

Notes:

(1)Pulse width limited by safe operating area

(2)I_{SD} ≤ 9 A, di/dt ≤ 100 A/µs; V_{DS} peak < $V_{(BR)DSS}$

(3)V_{DS} ≤ 760 V

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.39	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient	62.5	°C/W

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	3	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	90	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 5: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	950			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 950 V			1	µA
		V_{GS} = 0 V, V_{DS} = 950 V T_C = 125 °C(1)			50	µA
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = ±20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DD} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 3 A		1	1.25	Ω

Notes:

(1) Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	450	-	pF
C_{oss}	Output capacitance		-	30	-	pF
C_{rss}	Reverse transfer capacitance		-	1.6	-	pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{DS} = 0 to 760 V, V_{GS} = 0 V	-	45	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related		-	19	-	pF
R_g	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 760 V, I_D = 6 A V_{GS}= 0 to 10 V (see *Figure 15: "Test circuit for gate charge behavior"*)	-	13	-	nC
Q_{gs}	Gate-source charge		-	3	-	nC
Q_{gd}	Gate-drain charge		-	7	-	nC

Notes:

(1) $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

(2) $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}= 475 V, I_D = 3 A, R_G = 4.7 Ω V_{GS} = 10 V (see *Figure 14: "Test circuit for resistive load switching times"* and *Figure 19: "Switching time waveform"*)	-	12	-	ns
t_r	Rise time		-	12	-	ns
$t_{d(off)}$	Turn-off delay time		-	33	-	ns
t_f	Fall time		-	21	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
I_{SDM}(1)	Source-drain current (pulsed)		-		36	A
V_{SD}(2)	Forward on voltage	I_{SD} = 6 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 6 A, di/dt = 100 A/µs, V_{DD} = 60 V (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	372		ns
Q_{rr}	Reverrse recovery charge		-	4		µC
I_{RRM}	Reverse recovery current		-	22		A
t_{rr}	Reverse recovery time	I_{SD} = 6 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	522		ns
Q_{rr}	Reverse recovery charge		-	5		µC
I_{RRM}	Reverse recovery current		-	20		A

Notes:

(1)Pulse width limited by safe operating area

(2)Pulsed: pulse duration = 300 µs, duty cycle 1.5%

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ±1 mA, I_D = 0 A	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

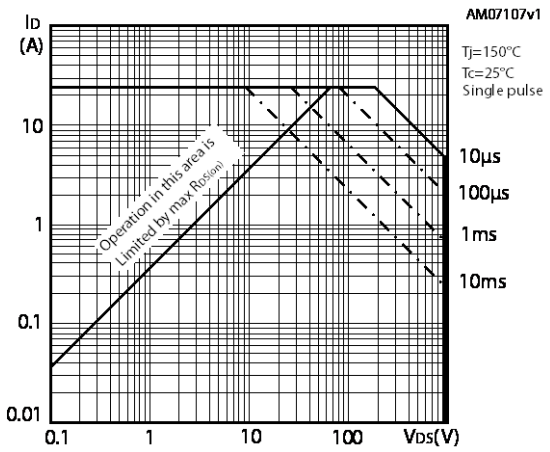


Figure 3: Thermal impedance

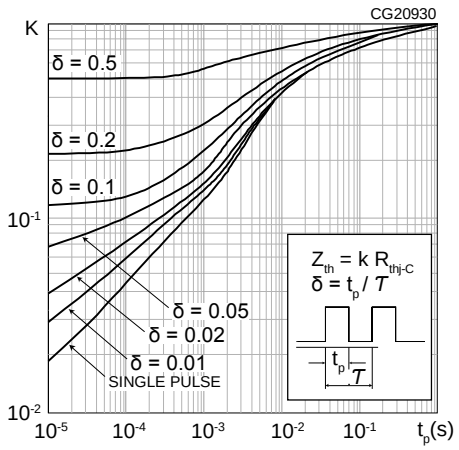


Figure 4: Output characteristics

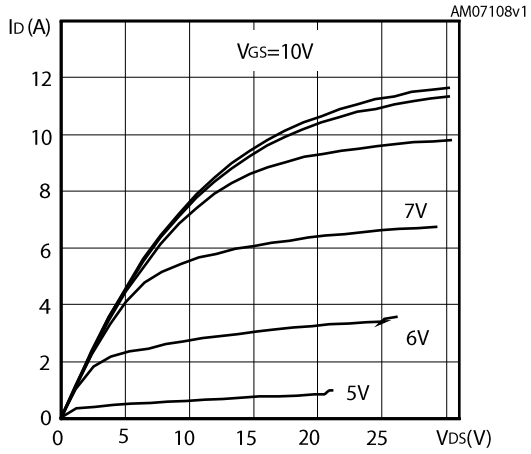


Figure 5: Transfer characteristics

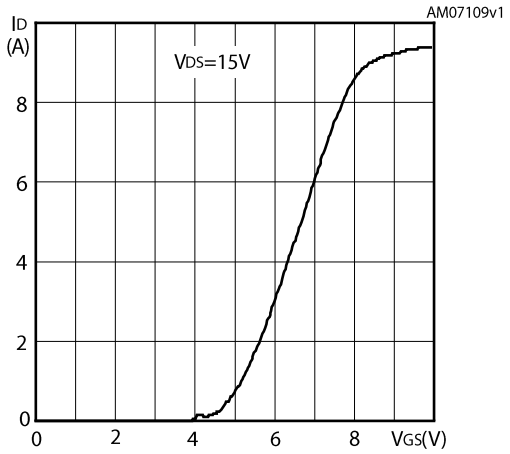


Figure 6: Gate charge vs gate-source voltage

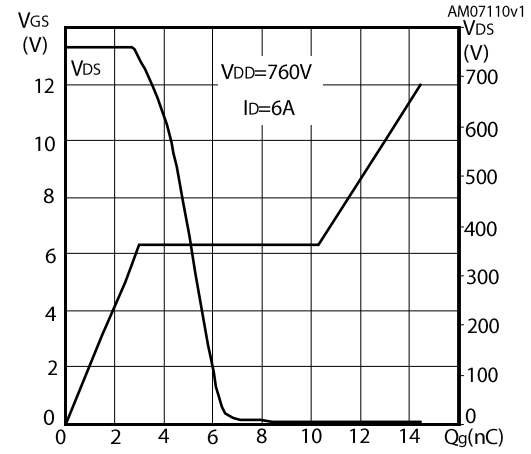


Figure 7: Static drain-source on-resistance

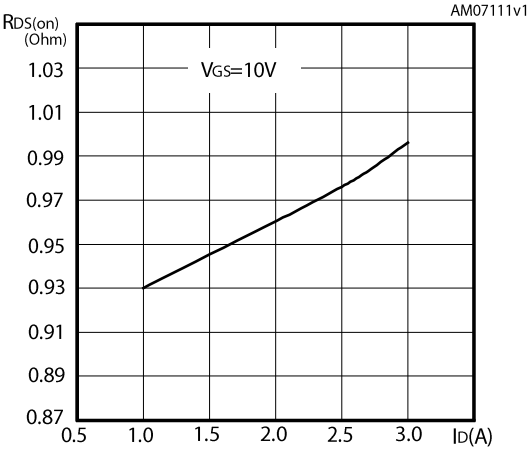


Figure 8: Capacitance variations

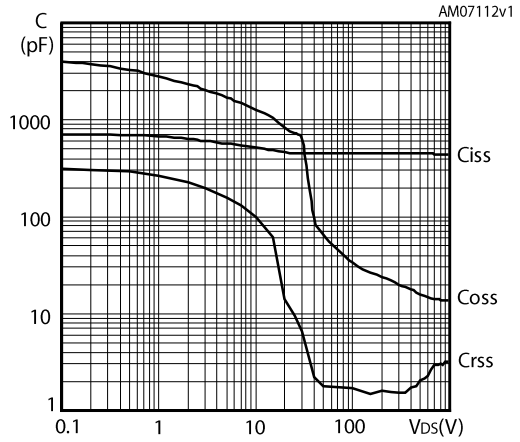


Figure 9: Normalized gate threshold voltage vs temperature

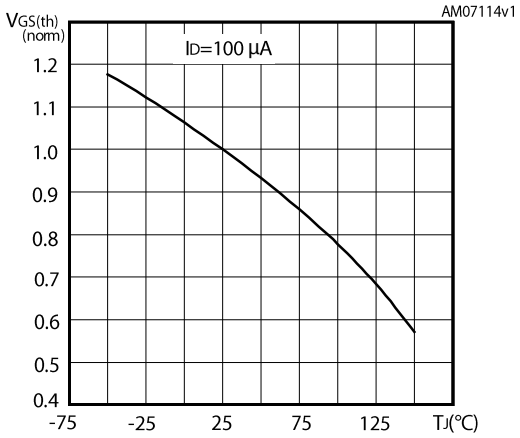


Figure 10: Normalized on-resistance vs temperature

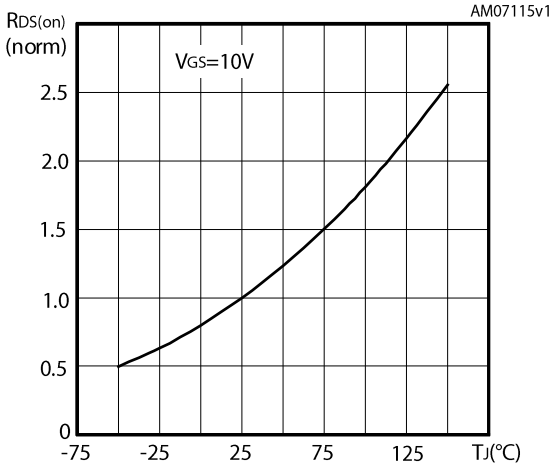


Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

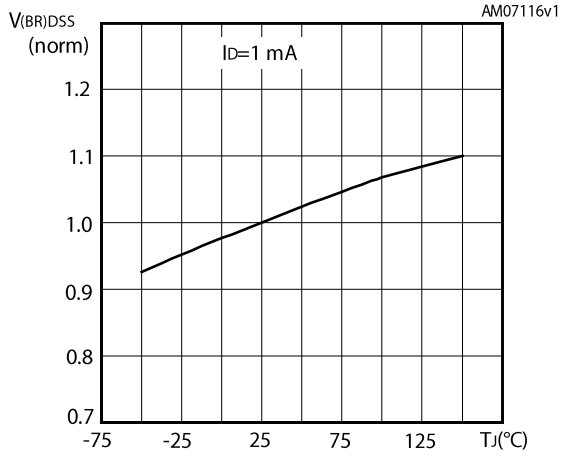


Figure 12: Maximum avalanche energy vs starting T_J

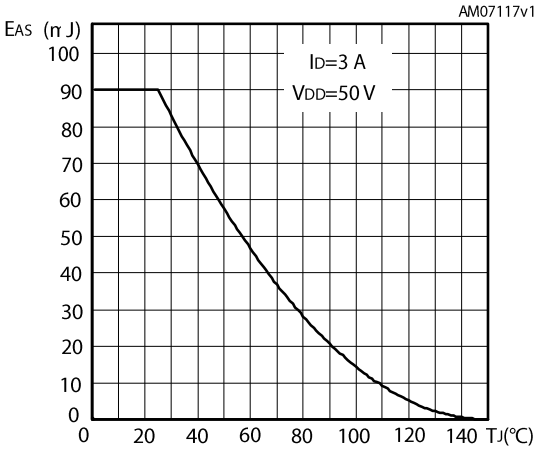
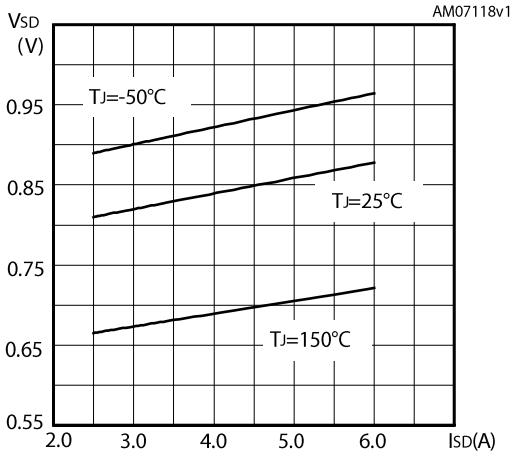


Figure 13: Source-drain diode forward characteristics



3 Test circuits

Figure 14: Test circuit for resistive load switching times

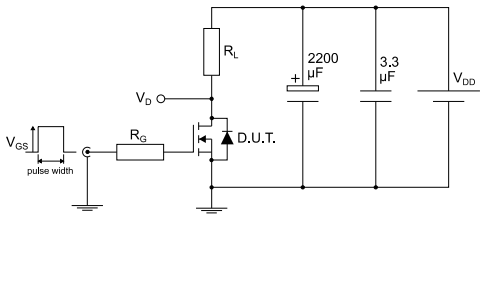


Figure 15: Test circuit for gate charge behavior

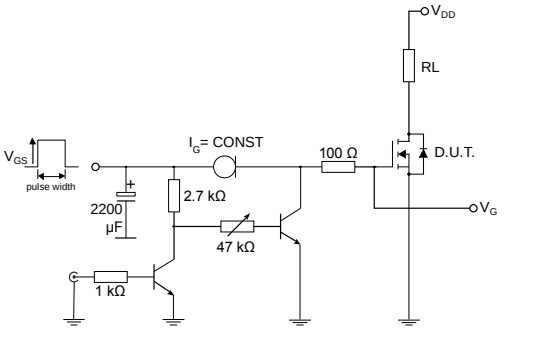


Figure 16: Test circuit for inductive load switching and diode recovery times

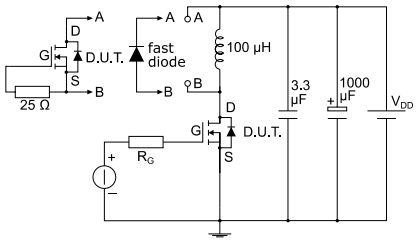


Figure 17: Unclamped inductive load test circuit

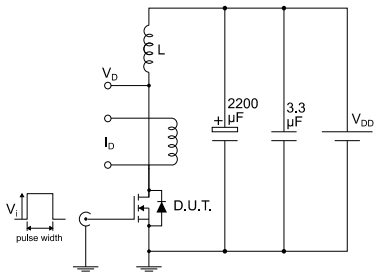


Figure 18: Unclamped inductive waveform

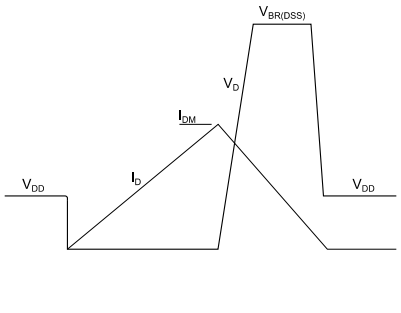
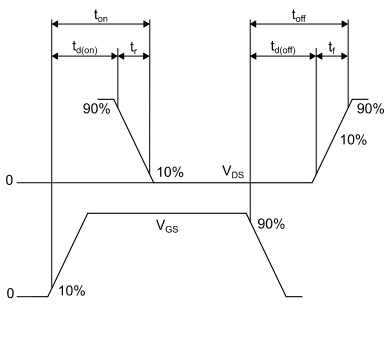


Figure 19: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 I²PAK package information

Figure 20: I²PAK package outline

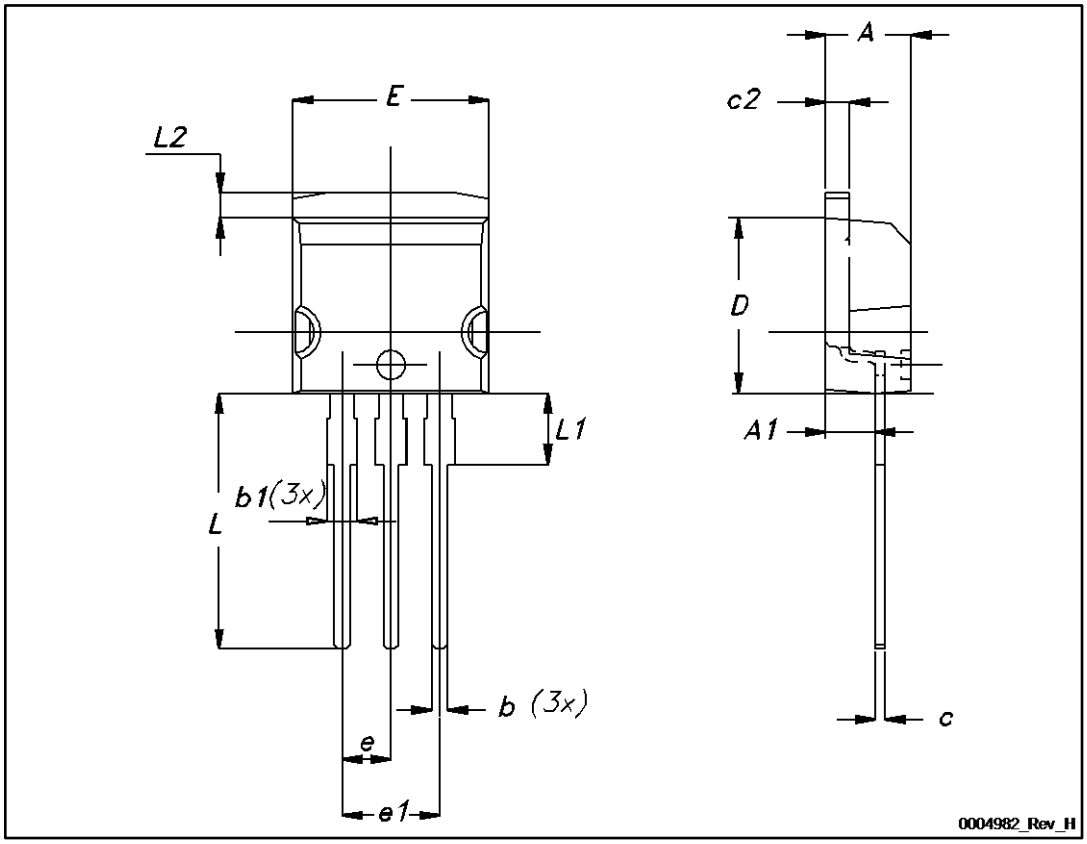


Table 10: I²PAK package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	-	4.60
A1	2.40	-	2.72
b	0.61	-	0.88
b1	1.14	-	1.70
c	0.49	-	0.70
c2	1.23	-	1.32
D	8.95	-	9.35
e	2.40	-	2.70
e1	4.95	-	5.15
E	10	-	10.40
L	13	-	14
L1	3.50	-	3.93
L2	1.27	-	1.40

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
03-May-2017	1	First release.

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